



April 1999  
PRELIMINARY

# FDS3580

## 80V N-Channel PowerTrench™ MOSFET

### General Description

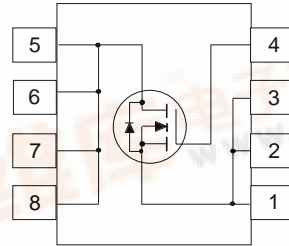
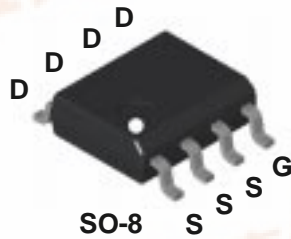
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable  $R_{DS(ON)}$  specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

### Features

- 7.6 A, 80 V.  $R_{DS(ON)} = 0.027 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 0.031 \Omega @ V_{GS} = 6 \text{ V}$ .
- Low gate charge (34nC typical).
- Fast switching speed.
- High performance trench technology for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.



### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DSS}$	Drain-Source Voltage	80	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current - Continuous (Note 1a)	7.6	A
	- Pulsed	50	
$P_D$	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1	
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	°C/W

### Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS3580	FDS3580	13"	12mm	2500 units



## Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_j}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		81		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V			1	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA

### On Characteristics (Note 2)

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	2.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_j}$	Gate Threshold Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		-7		mV/°C
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.6 A V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.6 A, T <sub>J</sub> = 125°C V <sub>GS</sub> = 6 V, I <sub>D</sub> = 7 A		0.022 0.037 0.024	0.027 0.055 0.031	Ω
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	30			A
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 7.6 A		28		S

### Dynamic Characteristics

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		1800		pF
C <sub>oss</sub>	Output Capacitance			180		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			90		pF

### Switching Characteristics (Note 2)

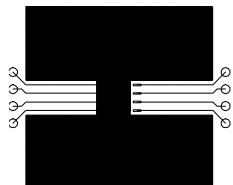
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 40 V, I <sub>D</sub> = 1 A, V <sub>GS</sub> = 10 V, R <sub>GEN</sub> = 6 Ω		13	26	ns
t <sub>r</sub>	Turn-On Rise Time			8	20	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			34	60	ns
t <sub>f</sub>	Turn-Off Fall Time			16	30	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 7.6 A, V <sub>GS</sub> = 10 V		34	46	nC
Q <sub>gs</sub>	Gate-Source Charge			6.1		nC
Q <sub>gd</sub>	Gate-Drain Charge			6.9		nC

### Drain-Source Diode Characteristics and Maximum Ratings

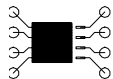
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current			2.1		A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.1 A <small>(Note 2)</small>		0.74	1.2	V

#### Notes:

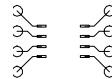
- 1: R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θCA</sub> is determined by the user's board design.



a) 50° C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz. copper.



b) 105° C/W when mounted on a 0.04 in<sup>2</sup> pad of 2 oz. copper.



c) 125° C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- 2: Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

## Typical Characteristics

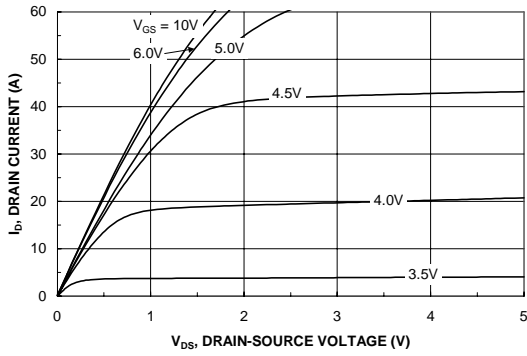


Figure 1. On-Region Characteristics.

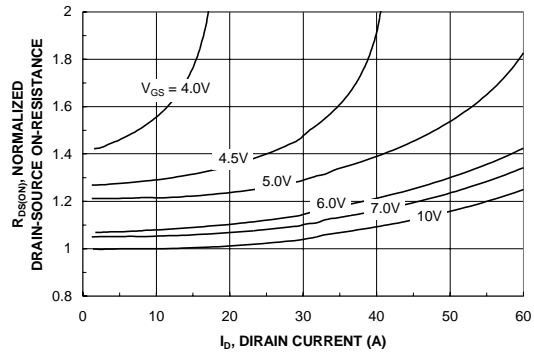


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

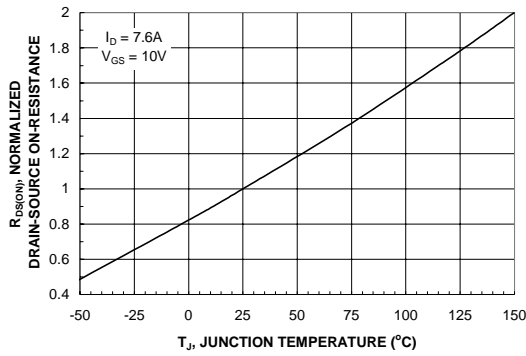


Figure 3. On-Resistance Variation with Temperature.

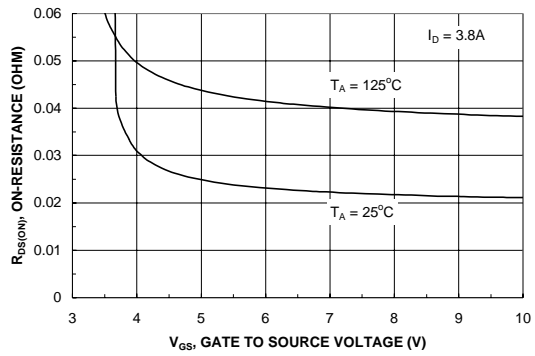


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

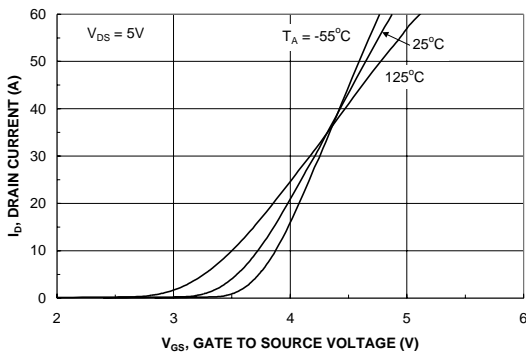


Figure 5. Transfer Characteristics.

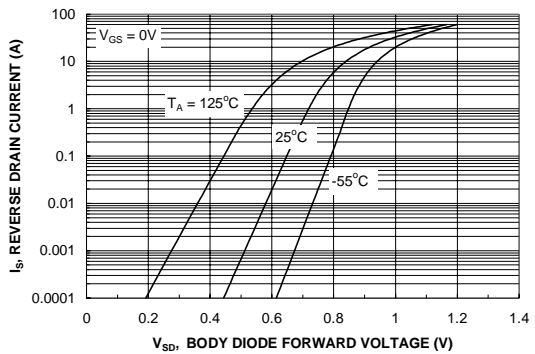
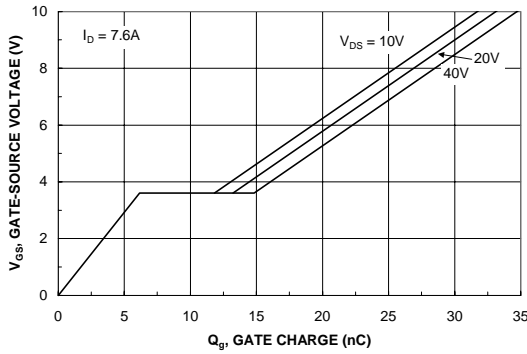
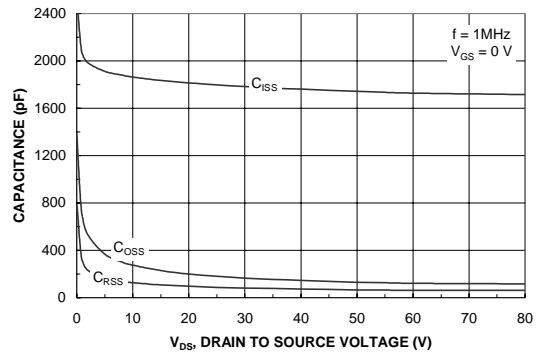


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

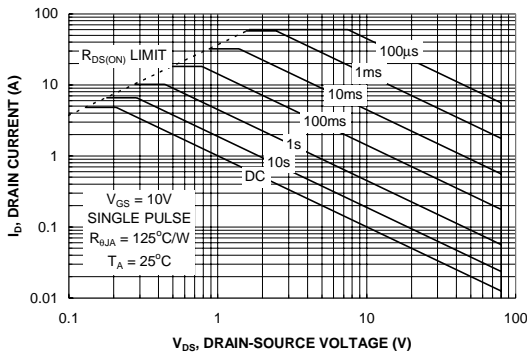
**Typical Characteristics** (continued)



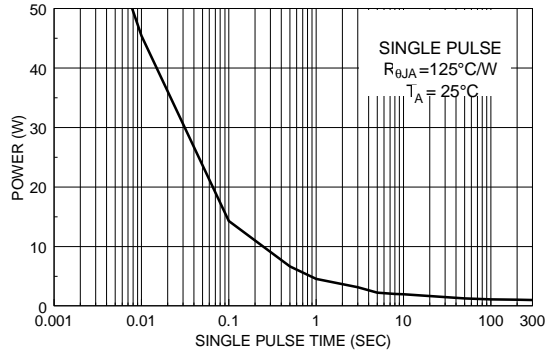
**Figure 7. Gate-Charge Characteristics.**



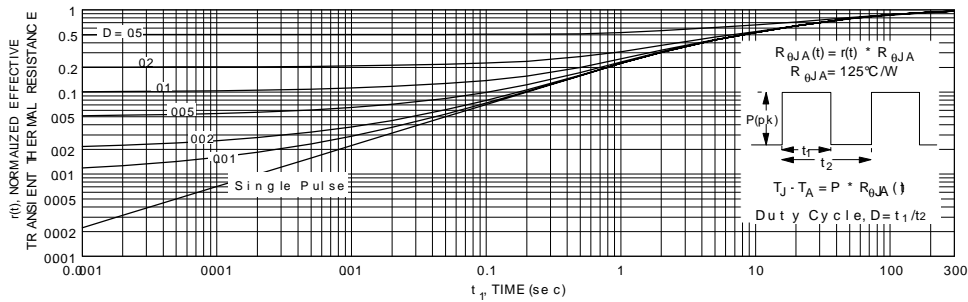
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



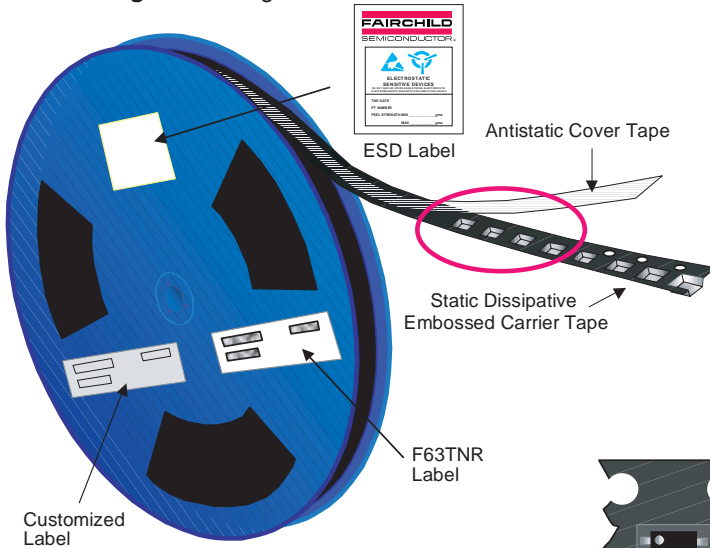
**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

# SO-8 Tape and Reel Data and Package Dimensions



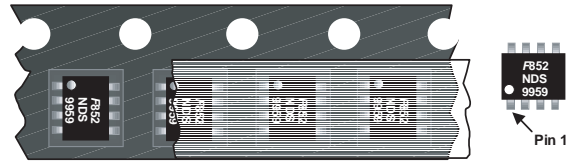
## SOIC(8lds) Packaging Configuration: Figure 1.0



### Packaging Description:

SOIC-8 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 330cm diameter reel. The reels are dark blue in color and is made of polystyrene plastic (anti-static coated). Other option comes in 500 units per 7" or 177cm diameter reel. This and some other options are further described in the Packaging Information table.

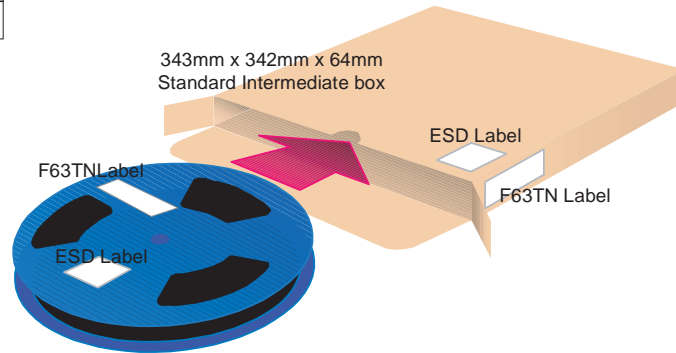
These full reels are individually barcode labeled and placed inside a standard intermediate box (illustrated in figure 1.0) made of recyclable corrugated brown paper. One box contains two reels maximum. And these boxes are placed inside a barcode labeled shipping box which comes in different sizes depending on the number of parts shipped.



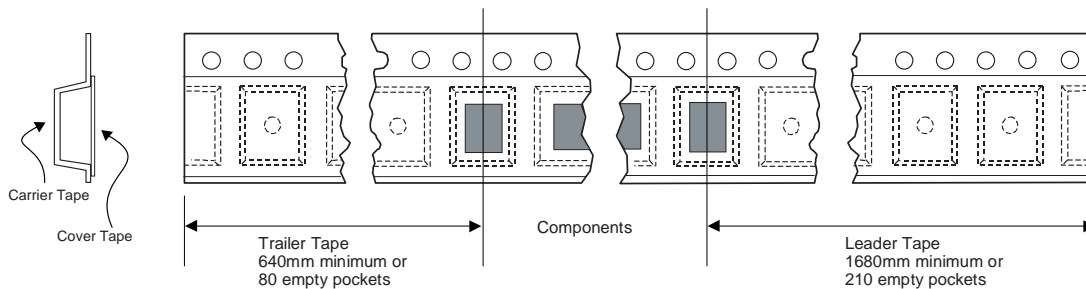
SOIC-8 Unit Orientation

SOIC (8lds) Packaging Information				
Packaging Option	Standard (no flow code)	L86Z	F011	D84Z
Packaging type	TNR	Rail/Tube	TNR	TNR
Qty per Reel/Tube/Bag	2,500	95	4,000	500
Reel Size	13" Dia	-	13" Dia	7" Dia
Box Dimension (mm)	343x64x343	530x130x83	343x64x343	184x187x47
Max qty per Box	5,000	30,000	8,000	1,000
Weight per unit (gm)	0.0774	0.0774	0.0774	0.0774
Weight per Reel (kg)	0.6060	-	0.9696	0.1182
Note/Comments				

### F63TNR Label sample

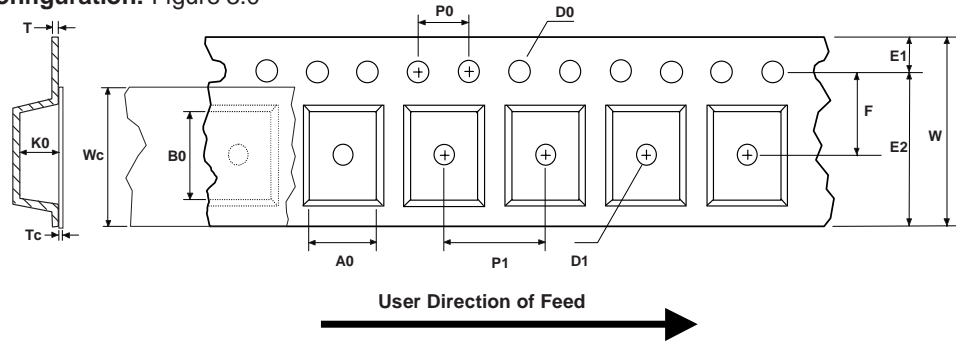


## SOIC(8lds) Tape Leader and Trailer Configuration: Figure 2.0



# SO-8 Tape and Reel Data and Package Dimensions, continued

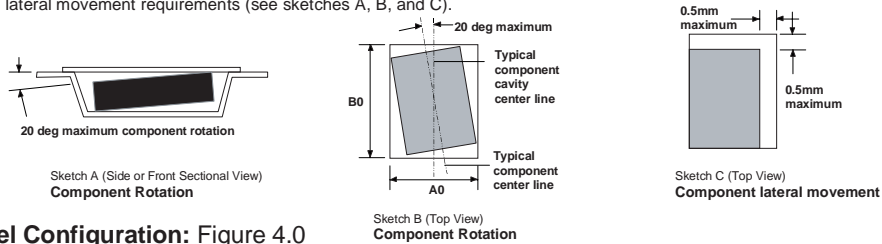
## SOIC(8lds) Embossed Carrier Tape Configuration: Figure 3.0



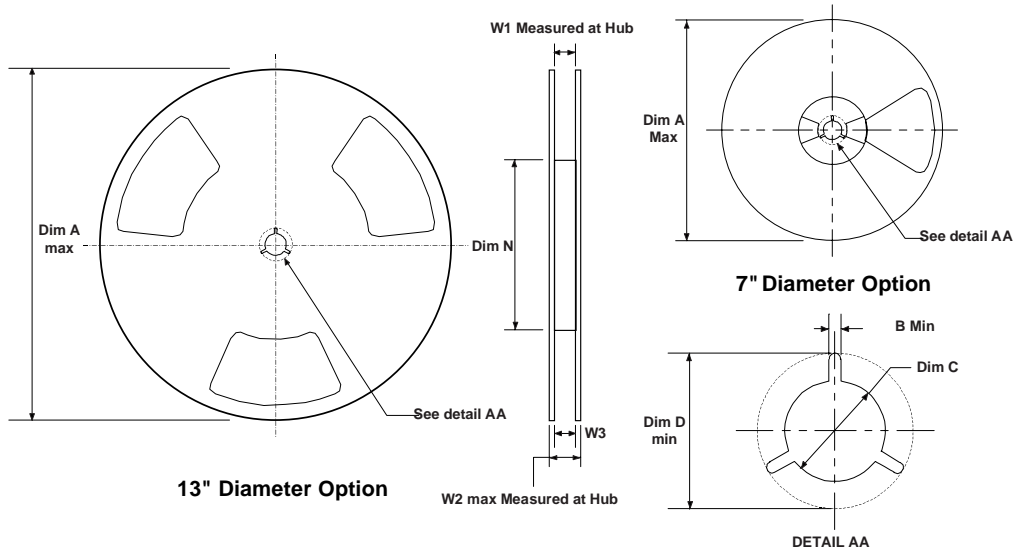
Dimensions are in millimeter

Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SOIC(8lds) (12mm)	6.50 +/-0.10	5.30 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	2.1 +/-0.10	0.450 +/- 0.150	9.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



## SOIC(8lds) Reel Configuration: Figure 4.0

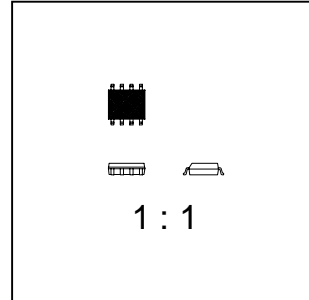
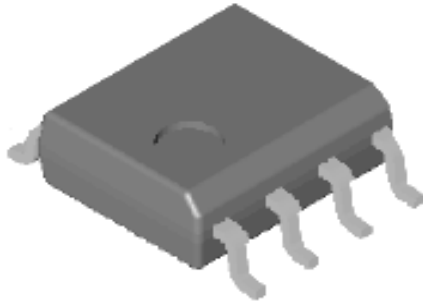


Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

# SO-8 Tape and Reel Data and Package Dimensions, continued

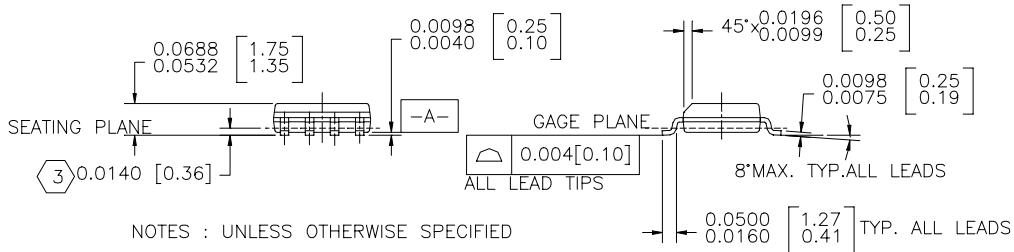
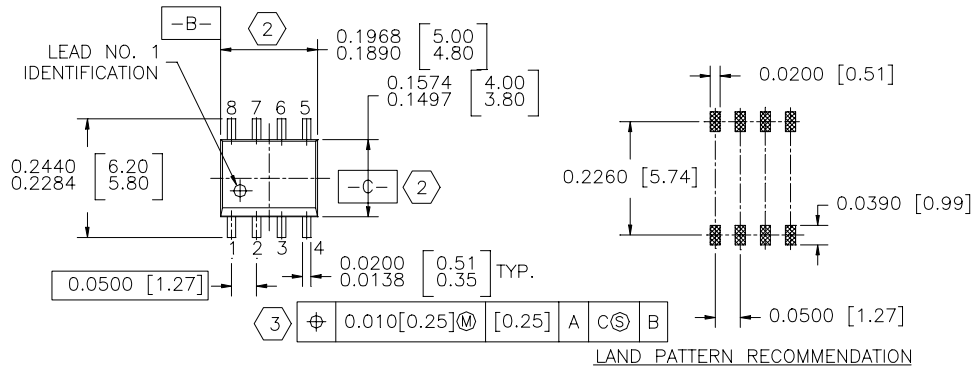
## SOIC-8 (FS PKG Code S1)



Scale 1:1 on letter size paper

Dimensions shown below are in:  
inches [millimeters]

Part Weight per unit (gram): 0.0774



NOTES : UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH:  
200 MICROINCHES / 5.08 MICRONS MINIMUM  
LEAD / TIN (SOLDER) ON COPPER.

SO 0.150 WIDE 8 LEADS

2. THESE DIMENSIONS DO NOT INCLUDE MOLD FLASH

3. MAXIMUM LEAD 0.024 [0.609]

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FACT™	QFET™	
FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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